L Number	Hits	Search Text	DB	Time stamp
40	1	09/641125	USPAT;	2004/02/22 20:28
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	20.20
41	11	"5885747"	USPAT; US-PGPUB; EPO; JPO;	2004/02/22 20:39
42	4588	(250/200,492.1,492.22,492.3).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/22 20:40
43	2726	(electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/22 20:41
44	504	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two or compensation) near2 mask)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:42
45	502	<u> </u>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:43
46	65		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:43
47	64	l · · · · · · · · · · · · · · · · · · ·	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:44
48	55	•	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:45
49	40	<pre>((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46
50	24	optic\$4) or lens) (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46

51	20	((((((electron or charged-particle or	USPAT;	2004/02/22
51	20	<pre>((((((((((((((((((((((((((((((((((((</pre>	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	20:53
52	12	<pre>((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47
53	2		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
54		<pre>((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47

			tronam.	2004/02/22
55	3	<pre>((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3)) and defect\$4</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
56	3	<pre>(((((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and ((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:49
57	2	photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3)) and defect\$4) and control\$5 ((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask)) and (location or adddress\$3) and stor\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:52
58	1	"5885747".PN.	USPAT	2004/02/22 20:51
59	0	6645676.URPN.	USPAT	2004/02/22 20:52
60	0	10/657429	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:52
61	30	<pre>(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and ((second or two) near2 mask)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53

62	4	<pre>((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and ((second or two) near2 mask)) and (location or adddress\$3)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
63	3	and stor\$3 ((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and ((second or two) near2 mask)) and (location or adddress\$3) and stor\$3) and defect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55

L Number	Hits	Search Text	DB	Time stamp
40	1	09/641125	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/22 20:28
41	11	"5885747"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/22 20:39
42	4588	(250/200,492.1,492.22,492.3).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:40
43	2726	(electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 21:05
44	504	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two or compensation) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:42
45	502	_	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:43
46	65	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:43
47	64		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:44
48	55	1 •	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 . 20:45
49	40	<pre>((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46
50	24	•	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46

	1		TIGDAM :	[0004/00/00
51	20	<pre>((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53
52	12	mask) ((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47
53	2	(charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and ((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
54	8	stor\$3 (((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47
		<pre>((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3)</pre>		

			Manage .	1 2004 /00 /00
55	3	<pre>((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3)) and defect\$4</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
56	3	<pre>((((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:49
57	2	mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask))) and (location or adddress\$3)) and defect\$4) and control\$5 (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and (second near2 mask)) and (location or adddress\$3) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:52
58	1	stor\$3 "5885747".PN.	USPAT	2004/02/22
59	0	6645676.URPN.	USPAT	20:51 2004/02/22
60	0	10/657429	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	20:52 2004/02/22 20:52
61	30	<pre>(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and ((second or two) near2 mask)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53

			T	
62	4	<pre>((((((((((((((((((((((((((((((((((((</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:01
63	3	and stor\$3 (((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((plurality or multiple or two) near2 mask)) and (compensat\$5 near2 mask)) and pattern\$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic\$4) or lens)) and ((second or two) near2 mask)) and (location or adddress\$3) and stor\$3) and defect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:58
64	133	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((250/200,492.1,492.22,492.3).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:58
65	133	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:58
66	6	((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage) and (main near expos\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 20:59
67	0	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage) and (main near expos\$5)) and compensat\$5 near2 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:59
68	0	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage) and (main near expos\$5)) and (compensat\$5 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:59
69	46	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and (main near expos\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:00
70	20	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and (main near expos\$5)) and defect\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:01
71		(charged adj particle)) and exposure and mask and stage and compensat\$5) and (main near expos\$5)) and defect\$5) and lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:01
72	8	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat\$5) and (main near expos\$5)) and defect\$5) and lens) and (location or adddress\$3) and stor\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 21:03

			IICDAM.	2004/02/22
73	8	(((((electron or charged-particle or	USPAT;	2004/02/22
		(charged adj particle)) and exposure and	US-PGPUB;	21:03
		mask and stage and compensat\$5) and (main	EPO; JPO;	
		near expos\$5)) and defect\$5) and lens)	DERWENT;	
	·	and (location or adddress\$3) and stor\$3)	IBM_TDB	
		and (resist or film or photoresist)		
74	8	((((((electron or charged-particle or	USPAT;	2004/02/22
		(charged adj particle)) and exposure and	US-PGPUB;	21:04
		mask and stage and compensat\$5) and (main	EPO; JPO;	
		near expos\$5)) and defect\$5) and lens)	DERWENT;	
		and (location or adddress\$3) and stor\$3)	IBM TDB	
		and (resist or film or photoresist)) and	_	
		((plurality or several or two or		
Ì		multiple) near2 mask)		
75	8	((((((electron or charged-particle or	USPAT;	2004/02/22
		(charged adj particle)) and exposure and	US-PGPUB;	21:05
		mask and stage and compensat\$5) and (main	EPO; JPO;	
		near expos\$5)) and defect\$5) and lens)	DERWENT;	
		and (location or adddress\$3) and stor\$3)	IBM TDB	
		and (resist or film or photoresist)) and	-	
1		((plurality or several or two or		
		multiple) near2 mask)) and ((electron or		
		charged-particle or (charged adj		
		particle)) near beam) and exposure and		
	1	mask and stage and compensat\$5		
	1	mask and stage and compensates		